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INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

APPLICANT(S)
Mitsutoshi MIYASAKAFILING DATE
March 19, 2002

GROUP

JCS71 U.S. PTO
10/099963
03/19/02

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
LP ↓	5,858,819	01/1999	Miyasaka		
	5,827,773	05/1997	Voutsas		
	6,066,516	5/2000	Miyasaka		
	6,017,719	1/2000	Yiyasaka		
	5,904,770	5/1999	Ohtani et al.		
	6,074,901	6/2000	Ohtani et al.		
	6,121,660	9/2000	Yamazaki et al.		
	6,113,689	9/2000	Moon		

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
LP ↓	JP-A-4-298020	10/1992	Japan	
	JP-A-4-100210	4/1992	Japan	
	JP-A-8-107067	4/1996	Japan	
	5-129332	5/1993	Japan	
	3-292719	12/1991	Japan	
	3-178124	8/1991	Japan	
	3-72617	3/1991	Japan	
	62-104021	5/1987	Japan	
	6-216044	8/1994	Japan	
	63-151014	6/1988	Japan	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

LP	Levinson, J., et al., "Conductivity Behavior in Polycrystalline Semiconductor Thin Film Transistors," <u>J. Appl. Phys.</u> 53 (2), February 1982, pp. 1193-1202.
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EXAMINER

LON G ATOM

DATE CONSIDERED

7/9/03

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: March 19, 2002